

Amendments to the Claims:

Please cancel claim 5 as follows. Please amend claims 16, and 7 as follows.

This listing of claims replaces all prior versions, and listings, of claims in the application.

Listing of claims:

1. (currently amended) An electrode line structure of a semiconductor device comprising:
a semiconductor substrate; and
electrode lines on the semiconductor substrate, the electrode lines each having an inclined outer end in the long axis direction, wherein each electrode line comprises a conductive layer and a hard mask layer;

wherein the electrode lines comprise one of word lines and bit lines of the semiconductor device, and wherein the electrode lines each includes a first line unit, which substantially functions as an electrode line, and a second line unit, which includes the inclined outer end in the long axis direction and which is separated from the first line unit by a hole that is formed through the conductive layer and the hard mask layer of each electrode line, wherein the hole has a width between a hard mask layer portion of the first line unit and a hard mask layer portion of the second line unit, the width being substantially the same as a width between a conductive layer portion of the first line unit and a conductive layer portion of the second line unit predetermined distance, and wherein each electrode line further includes an insulating plug[[],] which is positioned in the hole interposed between the first line unit and the second line unit and electrically insulates the first line unit from the second line unit, the insulating plug having an upper surface that is at a same level as [[an]]the upper surface of the hard mask layer portion of the first line unit and [[an]] the upper surface of the hard mask layer portion of the second line unit, wherein the insulating plug has a width between the hard mask layer portion of the first line unit and the hard mask layer portion of the second line unit, the width being substantially the same as a width between the conductive layer portion of the first line unit and the conductive layer portion of the second line unit.

2. (previously presented) The electrode line structure of claim 1, wherein a first length (X1) of the electrode lines is greater than a second length (X2) by at least a predetermined third length (X3).
3. (previously presented) The electrode line structure of claim 2, wherein the insulating plug is formed at a predetermined position of each of the electrode lines such that the first line unit has the second length (X2).
4. (previously presented) The electrode line structure of claim 2, wherein the third length (X3) is the length of the second line unit and is greater than a width of the electrode lines and less than the second length (X2).
5. (canceled)
6. (currently amended) The electrode line structure of claim [[5]]1, wherein the conductive layer comprises a material containing tungsten.
7. (currently amended) The electrode line structure of claim [[5]]1, wherein the hard mask layer comprises a silicon nitride layer or a silicon oxynitride layer.
8. (previously presented) The electrode line structure of claim 1, wherein a spacer is formed on the inclined outer end in the long axis direction of the second line unit.
9. (original) The electrode line structure of claim 8, wherein the insulating plug is formed of a material of which the spacer is formed.
10. - 18. (canceled)